

# High Voltage Standard Rectifier Module

$$V_{RRM} = 2 \times 2200 \text{ V}$$

$$I_{FAV} = 310 \text{ A}$$

$$V_F = 1,03 \text{ V}$$


Phase leg

Part number

**MDD312-22N1**



Backside: isolated

 E72873



## Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

## Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

## Package: Y1

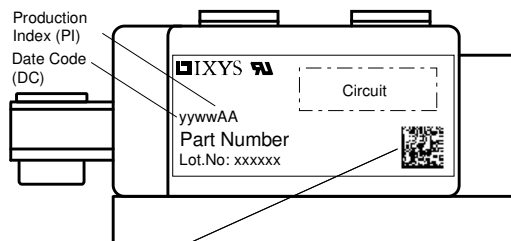
- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling

## Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					2300	V
$V_{RRM}$	max. repetitive reverse blocking voltage					2200	V
$I_R$	reverse current	$V_R = 2200\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		500	$\mu\text{A}$
		$V_R = 2200\text{ V}$		$T_{VJ} = 150^\circ\text{C}$		30	mA
$V_F$	forward voltage drop	$I_F = 300\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		1,13	V
		$I_F = 600\text{ A}$				1,33	V
		$I_F = 300\text{ A}$		$T_{VJ} = 125^\circ\text{C}$		1,03	V
		$I_F = 600\text{ A}$				1,29	V
$I_{FAV}$	average forward current	$T_C = 100^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		310	A
$I_{F(RMS)}$	RMS forward current	180° sine	d = 0.5			520	A
$V_{F0}$	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0,80	V
$r_F$	slope resistance					0,6	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0,12	K/W
$R_{thCH}$	thermal resistance case to heatsink				0,04		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		1040	W
$I_{FSM}$	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		10,8	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0\text{ V}$		11,7	kA
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		9,18	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0\text{ V}$		9,92	kA
$I^2t$	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		583,2	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0\text{ V}$		566,1	kA <sup>2</sup> s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		421,4	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0\text{ V}$		409,0	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 700\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		288	pF

Package Y1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			600	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				680		g
$M_D$	mounting torque		4,5		7	Nm
$M_T$	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	16,0			mm
$d_{Spb/Apb}$		terminal to backside	16,0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V



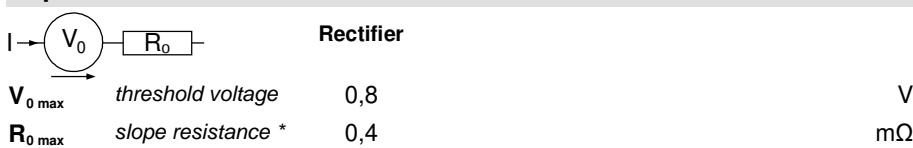
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD312-22N1	MDD312-22N1	Box	3	467278

Similar Part	Package	Voltage class
MDD312-12N1	Y1-CU	1200
MDD312-14N1	Y1-CU	1400
MDD312-16N1	Y1-CU	1600
MDD312-18N1	Y1-CU	1800

MDD312-20N1	Y1-CU	2000
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### Equivalent Circuits for Simulation \* on die level $T_{VJ} = 150^{\circ}\text{C}$





Outlines Y1





**Rectifier**

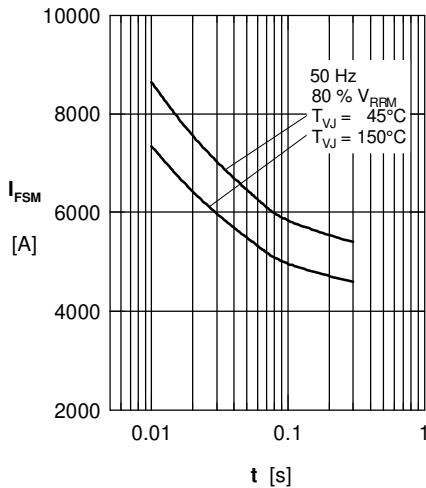


Fig. 1 Surge overload current  
 $I_{FSM}$ : Crest value,  $t$ : duration

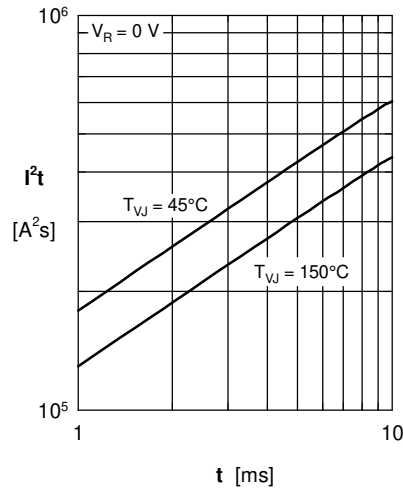


Fig. 2  $I^2t$  versus time (1-10 ms)

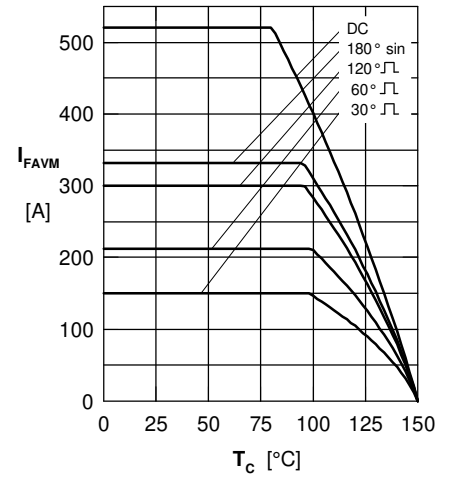


Fig. 3 Maximum forward current at case temperature

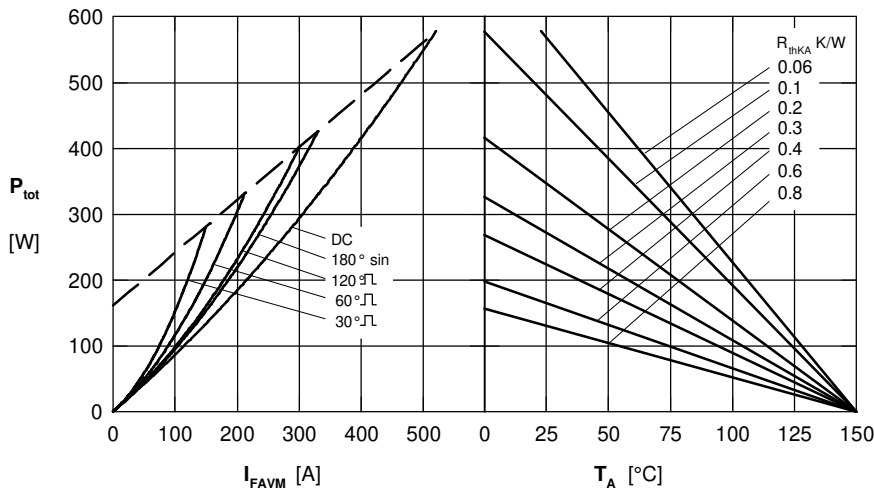


Fig. 4 Power dissipation vs. forward current & ambient temperature (per diode)

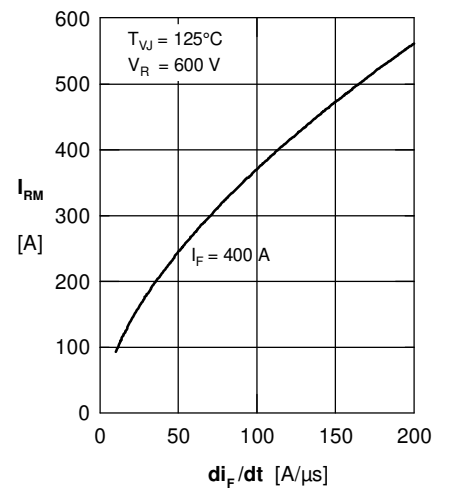


Fig. 5 Typ. peak reverse current

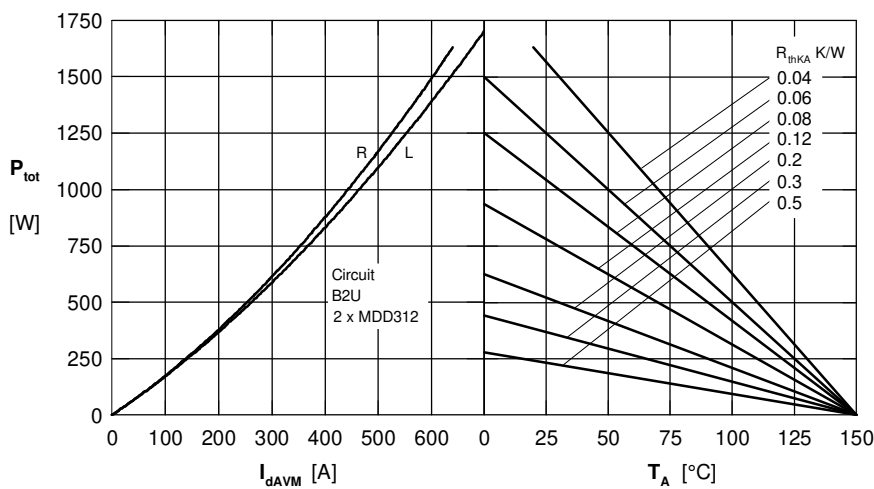


Fig. 6 Single phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature  $R$  = resistive load,  $L$  = inductive load

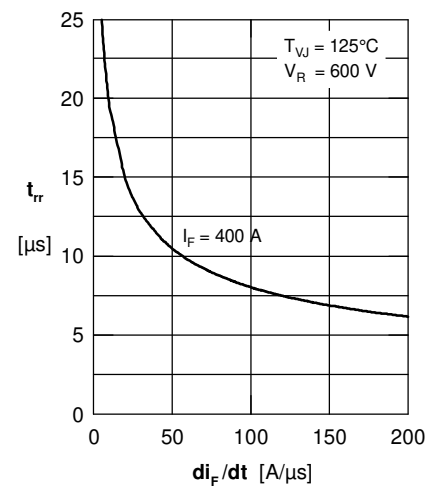


Fig. 7 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$



**Rectifier**



Fig. 8 Three phase rectifier bridge: Power dissipation vs. direct output current & ambient temperature



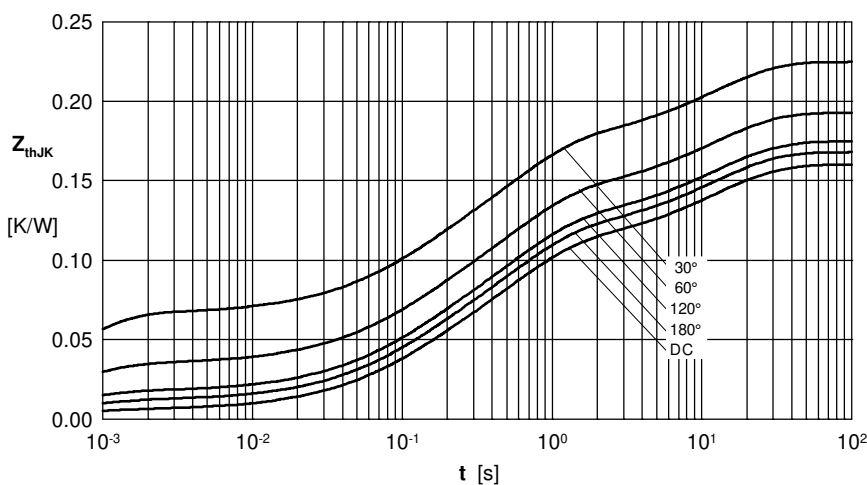
$R_{thJC}$  for various conduction angles  $d$ :

$d$	$R_{thJC}$ [K/W]
DC	0.120
180°	0.128
120°	0.135
60°	0.153
30°	0.185

Constants for  $Z_{thJC}$  calculation:

$i$	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.0058	0.00054
2	0.0310	0.09800
3	0.0720	0.54000
4	0.0112	12.0000

Fig. 9 Transient thermal impedance junction to case (per diode)



$R_{thJK}$  for various conduction angles  $d$ :

$d$	$R_{thJK}$ [K/W]
DC	0.160
180°	0.168
120°	0.175
60°	0.193
30°	0.225

Constants for  $Z_{thJK}$  calculation:

$i$	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.0058	0.00054
2	0.0310	0.09800
3	0.0720	0.54000
4	0.0112	12.0000
5	0.0400	12.0000

Fig. 10 Transient thermal impedance junction to heatsink (per diode)